Chennupati Jagadish

List of Publications by Year
in descending order

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1,153 papers	23,843 citations	13332 70 h-index	25230 113 g-index
1187 all docs	1187 docs citations	1187 times ranked	19172 citing authors

#	Article	IF	Citations
1	A New Strategy for Selective Area Growth of Highly Uniform InGaAs/InP Multiple Quantum Well Nanowire Arrays for Optoelectronic Device Applications. Advanced Functional Materials, 2022, 32, 2103057.	7.8	21
2	Semiconductor Nanowire Arrays for Highâ€Performance Miniaturized Chemical Sensing. Advanced Functional Materials, 2022, 32, 2107596.	7.8	16
3	Surfaceâ€Structured Cocatalyst Foils Unraveling a Pathway to Highâ€Performance Solar Water Splitting. Advanced Energy Materials, 2022, 12, 2102752.	10.2	11
4	Topical review: pathways toward cost-effective single-junction IIIâ€“V solar cells. Journal Physics D: Applied Physics, 2022, 55, 143002.	1.3	17
5	A hybrid random laser using dye with self-organized GaN nanorods. Semiconductor Science and Technology, 2022, 37, 025009.	1.0	2
6	Tuning the crystal structure and optical properties of selective area grown InGaAs nanowires. Nano Research, 2022, 15, 3695-3703.	5.8	5
7	Epitaxial Growth of GaAs Nanowires on Synthetic Mica by Metalâ€“Organic Chemical Vapor Deposition. ACS Applied Materials & Interfaces, 2022, 14, 3395-3403.	4.0	7
8	Protocol on the fabrication of monocrystalline thin semiconductor via crack-assisted layer exfoliation technique for photoelectrochemical water-splitting. STAR Protocols, 2022, 3, 101015.	0.5	1
9	A New Strategy for Selective Area Growth of Highly Uniform InGaAs/InP Multiple Quantum Well Nanowire Arrays for Optoelectronic Device Applications (Adv. Funct. Mater. 3/2022). Advanced Functional Materials, 2022, 32, .	7.8	1
10	Second order nonlinear frequency generation at the nanoscale in dielectric platforms. Advances in Physics: X, 2022, 7, .	1.5	1
11	Unique reflection from birefringent uncoated and gold-coated InP nanowire crystal arrays. Optics Express, 2022, 30, 3172.	1.7	1
12	IIIâ€“V Semiconductor Whispering-Gallery Mode Micro-Cavity Lasers: Advances and Prospects. IEEE Journal of Quantum Electronics, 2022, 58, 1-18.	1.0	2
13	Investigation of lightâ€“matter interaction in single vertical nanowires in ordered nanowire arrays. Nanoscale, 2022, 14, 3527-3536.	2.8	6
14	Flexible InPâ€“ZnO nanowire heterojunction light emitting diodes. Nanoscale Horizons, 2022, 7, 446-454.	4.1	8
15	Design of InAs nanosheet arrays with ultrawide polarization-independent high absorption for infrared photodetection. Applied Physics Letters, 2022, 120, .	1.5	6
16	Ultrathin transparent metal capping layer on metal oxide carrier-selective contacts for Si solar cells. European Physical Journal: Special Topics, 2022, 231, 2933-2939.	1.2	2
17	nâ€SnO_x as a Transparent Electrode and Heterojunction for pâ€InP Nanowire Light Emitting Diodes. Advanced Optical Materials, 2022, 10, .	3.6	4
18	Photonic materials: from fundamentals to applications. European Physical Journal: Special Topics, 2022, 231, 583-587.	1.2	3

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19	Recent Advances in Materials Design Using Atomic Layer Deposition for Energy Applications. Advanced Functional Materials, 2022, 32, .	7.8	34
20	Direct GaAs Nanowire Growth and Monolithic Lightâ€Emitting Diode Fabrication on Flexible Plastic Substrates. Advanced Photonics Research, 2022, 3, .	1.7	4
21	Self-frequency-conversion nanowire lasers. Light: Science and Applications, 2022, 11, 120.	7.7	13
22	Nonpolar AlxGa1â^'xN/AlyGa1â^'yN multiple quantum wells on GaN nanowire for UV emission. Nano Research, 2022, 15, 7670-7680.	5.8	4
23	Deep-Ultraviolet Photodetectors Based on Hexagonal Boron Nitride Nanosheets Enhanced by Localized Surface Plasmon Resonance in Al Nanoparticles. ACS Applied Nano Materials, 2022, 5, 7481-7491.	2.4	9
24	High-density individually addressable platinum nanoelectrodes for biomedical applications. Discover Materials, 2022, 2, .	1.0	2
25	Effective Passivation of InGaAs Nanowires for Telecommunication Wavelength Optoelectronics. Advanced Optical Materials, 2022, 10, .	3.6	5
26	Lasing from InP Nanowire Photonic Crystals on InP Substrate. Advanced Optical Materials, 2021, 9, 2001745.	3.6	8
27	Controlled Cracking for Large-Area Thin Film Exfoliation: Working Principles, Status, and Prospects. ACS Applied Electronic Materials, 2021, 3, 145-162.	2.0	10
28	Identifying carbon as the source of visible single-photon emission from hexagonal boron nitride. Nature Materials, 2021, 20, 321-328.	13.3	210
29	Nanowires: a New Horizon for Polarization-resolved Terahertz Time-domain Spectroscopy. , 2021, , .		0
30	Understanding the role of facets and twin defects in the optical performance of GaAs nanowires for laser applications. Nanoscale Horizons, 2021, 6, 559-567.	4.1	11
31	Passivation of InP solar cells using large area hexagonal-BN layers. Npj 2D Materials and Applications, 2021, 5, .	3.9	9
32	Earthâ€Abundant Amorphous Electrocatalysts for Electrochemical Hydrogen Production: A Review. Advanced Energy and Sustainability Research, 2021, 2, 2000071.	2.8	30
33	Electron-Selective Contact for GaAs Solar Cells. ACS Applied Energy Materials, 2021, 4, 1356-1364.	2.5	17
34	Nanomechanical behavior of single taper-free GaAs nanowires unravelled by in-situ TEM mechanical testing and molecular dynamics simulation. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2021, 806, 140866.	2.6	4
35	Understanding Shape Evolution and Phase Transition in InP Nanostructures Grown by Selective Area Epitaxy. Small, 2021, 17, e2100263.	5.2	7
36	Managing Resonant and Nonresonant Lasing Modes in GaAs Nanowire Random Lasers. Nano Letters, 2021, 21, 3901-3907.	4.5	18

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37	Postgrowth Shaping and Transport Anisotropy in Two-Dimensional InAs Nanofins. ACS Nano, 2021, 15, 7226-7236.	7.3	3
38	Ultralow Threshold, Single-Mode InGaAs/GaAs Multiquantum Disk Nanowire Lasers. ACS Nano, 2021, 15, 9126-9133.	7.3	19
39	Understanding, engineering, and modulating the growth of neural networks: An interdisciplinary approach. Biophysics Reviews, 2021, 2, .	1.0	4
40	2D Carrier Localization at the Wurtzite-Zincblende Interface in Novel Layered InP Nanomembranes. ACS Photonics, 2021, 8, 1735-1745.	3.2	10
41	Terahertz Full-polarization-state Detection by Nanowires. , 2021, , .		0
42	Selective area epitaxy of IIIâ€“V nanostructure arrays and networks: Growth, applications, and future directions. Applied Physics Reviews, 2021, 8, .	5.5	75
43	Epitaxially Grown InP Micro-Ring Lasers. Nano Letters, 2021, 21, 5681-5688.	4.5	16
44	Light Absorption in Nanowire Photonic Crystal Slabs and the Physics of Exceptional Points: The Shape Shifter Modes. Sensors, 2021, 21, 5420.	2.1	0
45	Thin silicon via crack-assisted layer exfoliation for photoelectrochemical water splitting. IScience, 2021, 24, 102921.	1.9	4
46	Surface-Tailored InP Nanowires via Self-Assembled Au Nanodots for Efficient and Stable Photoelectrochemical Hydrogen Evolution. Nano Letters, 2021, 21, 6967-6974.	4.5	13
47	Broadband GaAsSb Nanowire Array Photodetectors for Filter-Free Multispectral Imaging. Nano Letters, 2021, 21, 7388-7395.	4.5	36
48	Manipulating Intermediates at the Auâ€“TiO₂ Interface over InP Nanopillar Array for Photoelectrochemical CO₂ Reduction. ACS Catalysis, 2021, 11, 11416-11428.	5.5	48
49	Controlling the lasing modes in random lasers operating in the Anderson localization regime. Optics Express, 2021, 29, 33548.	1.7	7
50	Spatially dense integration of micron-scale devices from multiple materials on a single chip via transfer-printing. Optical Materials Express, 2021, 11, 3567.	1.6	17
51	Thermodynamic properties of metastable wurtzite InP nanosheets. Journal Physics D: Applied Physics, 2021, 54, 505112.	1.3	1
52	Selfâ€Powered InP Nanowire Photodetector for Singleâ€Photon Level Detection at Room Temperature. Advanced Materials, 2021, 33, e2105729.	11.1	18
53	Tunable Synthesis of 3D Niobium Oxynitride Nanosheets for Lithium-Ion Hybrid Capacitors with High Energy/Power Density. ACS Sustainable Chemistry and Engineering, 2021, 9, 14569-14578.	3.2	7
54	Effect of Au substrate and coating on the lasing characteristics of GaAs nanowires. Scientific Reports, 2021, 11, 21378.	1.6	5

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55	Role of defects and grain boundaries in the thermal response of wafer-scale hBN films. Nanotechnology, 2021, 32, 075702.	1.3	6
56	High-speed InGaAs/InP Quantum Well Nanowire Array Light Emitting Diodes at Telecommunication Wavelength. , 2021, , .		0
57	Improving our Peer Review Processâ€”Editorial. Applied Physics Reviews, 2021, 8, .	5.5	0
58	Lasing from GaAs Nanowires on Fe Films. , 2021, , .		0
59	Epitaxially-grown InP micro-ring lasers. , 2021, , .		0
60	Non-epitaxial carrier selective contacts for III-V solar cells: A review. Applied Materials Today, 2020, 18, 100503.	2.3	23
61	Engineering IIIâ€“V Semiconductor Nanowires for Device Applications. Advanced Materials, 2020, 32, e1904359.	11.1	43
62	Forward and Backward Switching of Nonlinear Unidirectional Emission from GaAs Nanoantennas. ACS Nano, 2020, 14, 1379-1389.	7.3	53
63	What Will We Carry Forward from This Time?. ACS Nano, 2020, 14, 14253-14254.	7.3	4
64	Monocrystalline InP Thin Films with Tunable Surface Morphology and Energy Band gap. ACS Applied Materials & Interfaces, 2020, 12, 36380-36388.	4.0	12
65	Solar Water Splitting: Over 17% Efficiency Standâ€Alone Solar Water Splitting Enabled by Perovskiteâ€Silicon Tandem Absorbers (Adv. Energy Mater. 28/2020). Advanced Energy Materials, 2020, 10, 2070122.	10.2	4
66	High-Throughput Electrical Characterization of Nanomaterials from Room to Cryogenic Temperatures. ACS Nano, 2020, 14, 15293-15305.	7.3	5
67	Three-Dimensional Ordered Macroporous TiO₂â€“TaO_xN_y Heterostructure for Photoelectrochemical Water Splitting. Journal of Physical Chemistry C, 2020, 124, 24135-24144.	1.5	4
68	Hole and Electron Effective Masses in Single InP Nanowires with a Wurtzite-Zincblende Homojunction. ACS Nano, 2020, 14, 11613-11622.	7.3	8
69	Impact of invasive metal probes on Hall measurements in semiconductor nanostructures. Nanoscale, 2020, 12, 20317-20325.	2.8	4
70	Facet-dependent growth of InAsP quantum wells in InP nanowire and nanomembrane arrays. Nanoscale Horizons, 2020, 5, 1530-1537.	4.1	8
71	Electrical Properties of Compact Drop-Casted Cu2SnS3 Films. Journal of Electronic Materials, 2020, 49, 6403-6409.	1.0	1
72	Facet-Related Non-uniform Photoluminescence in Passivated GaAs Nanowires. Frontiers in Chemistry, 2020, 8, 607481.	1.8	2

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73	A new Editor-in-Chief for APR. Applied Physics Reviews, 2020, 7, 010401.	5.5	0
74	Over 17% Efficiency Standâ€Alone Solar Water Splitting Enabled by Perovskiteâ€Silicon Tandem Absorbers. Advanced Energy Materials, 2020, 10, 2000772.	10.2	58
75	Highly regular rosette-shaped cathodoluminescence in GaN self-assembled nanodisks and nanorods. Nano Research, 2020, 13, 2500-2505.	5.8	6
76	Polarizationâ€Independent Indium Phosphide Nanowire Photodetectors. Advanced Optical Materials, 2020, 8, 2000514.	3.6	9
77	In situ passivation of GaAsSb nanowires for enhanced infrared photoresponse. Nanotechnology, 2020, 31, 244002.	1.3	13
78	Review on III-V Semiconductor Single Nanowire-Based Room Temperature Infrared Photodetectors. Materials, 2020, 13, 1400.	1.3	44
79	Cathodoluminescence visualisation of local thickness variations of GaAs/AlGaAs quantum-well tubes on nanowires. Nanotechnology, 2020, 31, 424001.	1.3	4
80	Characterization, Selection, and Microassembly of Nanowire Laser Systems. Nano Letters, 2020, 20, 1862-1868.	4.5	17
81	Highly uniform InGaAs/InP quantum well nanowire array-based light emitting diodes. Nano Energy, 2020, 71, 104576.	8.2	23
82	Improving the Morphology and Crystal Quality of AlN Grown on Two-Dimensional hBN. Crystal Growth and Design, 2020, 20, 1811-1819.	1.4	7
83	Phase tailoring and wafer-scale uniform hetero-epitaxy of metastable-phased corundum Î±-Ga2O3 on sapphire. Applied Surface Science, 2020, 513, 145871.	3.1	28
84	Strain distribution in wrinkled hBN films. Solid State Communications, 2020, 310, 113847.	0.9	12
85	IIIâ€“V Semiconductor Materials for Solar Hydrogen Production: Status and Prospects. ACS Energy Letters, 2020, 5, 611-622.	8.8	54
86	Design of Ultrathin InP Solar Cell Using Carrier Selective Contacts. IEEE Journal of Photovoltaics, 2020, 10, 1657-1666.	1.5	18
87	Multipolar analysis of second-harmonic generation in (111) Gallium Arsenide nanoparticles. Journal of Physics: Conference Series, 2020, 1461, 012185.	0.3	0
88	Active Nanophotonics [Scanning the Issue]. Proceedings of the IEEE, 2020, 108, 625-627.	16.4	1
89	Three-dimensional cross-nanowire networks recover full terahertz state. Science, 2020, 368, 510-513.	6.0	81
90	Exploring the band structure of Wurtzite InAs nanowires using photocurrent spectroscopy. Nano Research, 2020, 13, 1586-1591.	5.8	7

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91	Carrier dynamics and recombination mechanisms in InP twinning superlattice nanowires. Optics Express, 2020, 28, 16795.	1.7	7
92	Non-Degenerate Nonlinear Frequency Mixing in (110)-Grown GaAs Nanoresonators. , 2020, , .		0
93	Switching Second-Harmonic Forward to Backward Emission via GaAs Nanoantennas. , 2020, , .		0
94	Non-Degenerate Sum-Frequency Generation in (110)-Grown GaAs Nanoresonators. , 2020, , .		0
95	Multipolar analysis of second-harmonic generation in GaAs nanoparticles grown along different crystallographic directions. AIP Conference Proceedings, 2020, , .	0.3	0
96	Wavelength-tunable InAsP quantum dots in InP nanowires. Applied Physics Letters, 2019, 115, 053101.	1.5	7
97	Effect of Sn Addition on Epitaxial GaAs Nanowire Grown at Different Temperatures in Metalâ€“Organic Chemical Vapor Deposition. Crystal Growth and Design, 2019, 19, 5314-5319.	1.4	4
98	Strong Hot Carrier Effects in Single Nanowire Heterostructures. Nano Letters, 2019, 19, 5062-5069.	4.5	13
99	On the origin of dislocation generation and annihilation in Î± -Ga2O3 epilayers on sapphire. Applied Physics Letters, 2019, 115, .	1.5	37
100	Band alignment and band bending at Î±-Ga2O3/ZnO n-n isotype hetero-interface. Applied Physics Letters, 2019, 115, .	1.5	25
101	Understanding the Effect of Catalyst Size on the Epitaxial Growth of Hierarchical Structured InGaP Nanowires. Nano Letters, 2019, 19, 8262-8269.	4.5	4
102	Nanowire Quantum Dot Surface Engineering for High Temperature Single Photon Emission. ACS Nano, 2019, 13, 13492-13500.	7.3	22
103	Second-Harmonic Generation in (111) Gallium Arsenide Nanoantennas. , 2019, , .		0
104	High-Efficiency Solar Cells from Extremely Low Minority Carrier Lifetime Substrates Using Radial Junction Nanowire Architecture. ACS Nano, 2019, 13, 12015-12023.	7.3	31
105	Resonant harmonic generation in AlGaAs nanoantennas probed by cylindrical vector beams. Nanoscale, 2019, 11, 1745-1753.	2.8	26
106	Four-Dimensional Probing of Phase-Reaction Dynamics in Au/GaAs Nanowires. Nano Letters, 2019, 19, 781-786.	4.5	3
107	Design Principles for Fabrication of InP-Based Radial Junction Nanowire Solar Cells Using an Electron Selective Contact. IEEE Journal of Photovoltaics, 2019, 9, 980-991.	1.5	31
108	Introduction of TiO₂ in CuI for Its Improved Performance as a p-Type Transparent Conductor. ACS Applied Materials & Interfaces, 2019, 11, 24254-24263.	4.0	33

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109	Regaining a Spatial Dimension: Mechanically Transferrable Two-Dimensional InAs Nanofins Grown by Selective Area Epitaxy. Nano Letters, 2019, 19, 4666-4677.	4.5	25
110	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. Scientific Reports, 2019, 9, 8796.	1.6	24
111	InGaAsP as a Promising Narrow Band Gap Semiconductor for Photoelectrochemical Water Splitting. ACS Applied Materials & Interfaces, 2019, 11, 25236-25242.	4.0	21
112	Shape Engineering of InP Nanostructures by Selective Area Epitaxy. ACS Nano, 2019, 13, 7261-7269.	7.3	41
113	Largeâ€Area Hexagonal Boron Nitride for Surface Enhanced Raman Spectroscopy. Advanced Materials Technologies, 2019, 4, 1900220.	3.0	26
114	Multiwavelength Single Nanowire InGaAs/InP Quantum Well Light-Emitting Diodes. Nano Letters, 2019, 19, 3821-3829.	4.5	32
115	Tailoring Second-Harmonic Emission from (111)-GaAs Nanoantennas. Nano Letters, 2019, 19, 3905-3911.	4.5	66
116	Compositional Varied Coreâ€“Shell InGaP Nanowires Grown by Metalâ€“Organic Chemical Vapor Deposition. Nano Letters, 2019, 19, 3782-3788.	4.5	17
117	Unusual spin properties of InP wurtzite nanowires revealed by Zeeman splitting spectroscopy. Physical Review B, 2019, 99, .	1.1	14
118	Nanosails Showcasing Zn₃As₂ as an Optoelectronicâ€Grade Earth Abundant Semiconductor. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900084.	1.2	8
119	Ultrathin Ta₂O₅ electron-selective contacts for high efficiency InP solar cells. Nanoscale, 2019, 11, 7497-7505.	2.8	38
120	Unexpected benefits of stacking faults on the electronic structure and optical emission in wurtzite GaAs/GaInP core/shell nanowires. Nanoscale, 2019, 11, 9207-9215.	2.8	18
121	Ultrasensitive Mid-wavelength Infrared Photodetection Based on a Single InAs Nanowire. ACS Nano, 2019, 13, 3492-3499.	7.3	45
122	Nanoscale Transfer Printing for the Heterogeneous Integration of Semiconductor Nanowire Lasers. , 2019, , .		0
123	Electron selective contact for high efficiency core-shell nanowire solar cell. , 2019, , .		4
124	Large area hexagonal boron nitride coatings for SERS applications with silver nanoparticles. , 2019, , .		0
125	Engineering the Side Facets of Vertical [100] Oriented InP Nanowires for Novel Radial Heterostructures. Nanoscale Research Letters, 2019, 14, 399.	3.1	9
126	III-V Semiconductor Nanowire Photodetectors. , 2019, , .		0

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127	Threshold reduction and yield improvement of semiconductor nanowire lasers via processing-related end-facet optimization. Nanoscale Advances, 2019, 1, 4393-4397.	2.2	9
128	Axial pâ€n junction design and characterization for InP nanowire array solar cells. Progress in Photovoltaics: Research and Applications, 2019, 27, 237-244.	4.4	22
129	Solutionâ€Processed InAs Nanowire Transistors as Microwave Switches. Advanced Electronic Materials, 2019, 5, 1800323.	2.6	3
130	Optical Study of p-Doping in GaAs Nanowires for Low-Threshold and High-Yield Lasing. Nano Letters, 2019, 19, 362-368.	4.5	24
131	Broadband Metamaterial Absorbers. Advanced Optical Materials, 2019, 7, 1800995.	3.6	404
132	Exploiting defects in TiO₂ inverse opal for enhanced photoelectrochemical water splitting. Optics Express, 2019, 27, 761.	1.7	37
133	Hybrid Plasmonic Lasing from Zinc-Doped GaAs Nanowires up to Room Temperature. , 2019, , .		1
134	Engineering IIIâ€“V Nanowires for Optoelectronics: From Visible to Terahertz. , 2019, , .		0
135	Infrared imaging in nonlinear GaAs metasurfaces. , 2019, , .		0
136	Tailoring directional scattering of second-harmonic generation from (111)-GaAs nanoantennas. , 2019, , .		0
137	Switchable unidirectional second-harmonic emission through GaAs nanoantennas. , 2019, , .		0
138	Enhancement of radiation tolerance in GaAs/AlGaAs coreâ€“shell and InP nanowires. Nanotechnology, 2018, 29, 225703.	1.3	8
139	Transfer printing of semiconductor nanowire lasers. IET Optoelectronics, 2018, 12, 30-35.	1.8	7
140	Nonlinear Absorption Applications of CH₃NH₃PbBr₃ Perovskite Crystals. Advanced Functional Materials, 2018, 28, 1707175.	7.8	84
141	Temperature effects in contacts between a metal and a semiconductor nanowire near the degenerate doping. Nanotechnology, 2018, 29, 165202.	1.3	1
142	Nonlinear Optics: Nonlinear Absorption Applications of CH₃NH₃PbBr₃ Perovskite Crystals (Adv. Funct. Mater. 18/2018). Advanced Functional Materials, 2018, 28, 1870122.	7.8	3
143	Reducing Zn diffusion in single axial junction InP nanowire solar cells for improved performance. Progress in Natural Science: Materials International, 2018, 28, 178-182.	1.8	23
144	CdS/TiO₂ photoanodes via solution ion transfer method for highly efficient solar hydrogen generation. Nano Futures, 2018, 2, 015004.	1.0	19

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145	Tantalum Oxide Electron-Selective Heterocontacts for Silicon Photovoltaics and Photoelectrochemical Water Reduction. ACS Energy Letters, 2018, 3, 125-131.	8.8	127
146	Photoelectrochemical studies of InGaN/GaN MQW photoanodes. Nanotechnology, 2018, 29, 045403.	1.3	15
147	CuI-TiO2Composite Thin Film for Flexible Electronic Applications. , 2018, , .		1
148	Precise Positioning and Orientation of Nanowire Lasers in Regular and Patterned Surfaces. , 2018, , .		2
149	Room Temperature GaAsSb Array Photodetectors. , 2018, , .		1
150	Semiconductor Nanowires for Optoelectronics Applications. , 2018, , .		0
151	The Route to Nanoscale Terahertz Technology: Nanowire-based Terahertz Detectors and Terahertz Modulators. , 2018, , .		0
152	Tuning the morphology and structure of disordered hematite photoanodes for improved water oxidation:ÂA physical and chemical synergistic approach. Nano Energy, 2018, 53, 745-752.	8.2	29
153	Radial Growth Evolution of InGaAs/InP Multi-Quantum-Well Nanowires Grown by Selective-Area Metal Organic Vapor-Phase Epitaxy. ACS Nano, 2018, 12, 10374-10382.	7.3	26
154	Lightâ€“Matter interactions on the nanoscale. Beilstein Journal of Nanotechnology, 2018, 9, 2125-2127.	1.5	6
155	Three-leaf dart-shaped single-crystal BN formation promoted by surface oxygen. Applied Physics Letters, 2018, 113, 163101.	1.5	0
156	The effect of Sn addition on GaAs nanowire grown by vaporâ€“liquidâ€“solid growth mechanism. Nanotechnology, 2018, 29, 465601.	1.3	4
157	Vertically Emitting Indium Phosphide Nanowire Lasers. Nano Letters, 2018, 18, 3414-3420.	4.5	33
158	The effect of nitridation on the polarity and optical properties of GaN self-assembled nanorods. Nanoscale, 2018, 10, 11205-11210.	2.8	9
159	IIIâ€“V Semiconductor Single Nanowire Solar Cells: A Review. Advanced Materials Technologies, 2018, 3, 1800005.	3.0	75
160	Role of surface energy in nanowire growth. Journal Physics D: Applied Physics, 2018, 51, 283002.	1.3	33
161	Perovskite Photovoltaic Integrated CdS/TiO₂ Photoanode for Unbiased Photoelectrochemical Hydrogen Generation. ACS Applied Materials & Interfaces, 2018, 10, 23766-23773.	4.0	38
162	Indium phosphide based solar cell using ultra-thin ZnO as an electron selective layer. Journal Physics D: Applied Physics, 2018, 51, 395301.	1.3	28

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163	Flow modulation epitaxy of hexagonal boron nitride. 2D Materials, 2018, 5, 045018.	2.0	57
164	Identification and modulation of electronic band structures of single-phase Î²-(AlxGa1â^'x)2O3 alloys grown by laser molecular beam epitaxy. Applied Physics Letters, 2018, 113, .	1.5	43
165	Modal refractive index measurement in nanowire lasersâ€"a correlative approach. Nano Futures, 2018, 2, 035004.	1.0	8
166	Direct-coated Cu2SnS3 films from molecular solution inks for solar photovoltaics. Materials Science in Semiconductor Processing, 2018, 88, 120-126.	1.9	18
167	Giant optical pathlength enhancement in plasmonic thin film solar cells using core-shell nanoparticles. Journal Physics D: Applied Physics, 2018, 51, 295106.	1.3	42
168	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Coreâ€"Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. ACS Nano, 2018, 12, 7327-7334.	7.3	8
169	Nonlinear frequency conversion in optical nanoantennas and metasurfaces: materials evolution and fabrication. Opto-Electronic Advances, 2018, 1, 18002101-18002112.	6.4	65
170	Distinguishing cap and core contributions to the photoconductive terahertz response of single GaAs based coreâ€"shellâ€"cap nanowire detectors. Lithuanian Journal of Physics, 2018, 58, .	0.1	1
171	Resonant harmonic generation in AlGaAs nanoantennas using structured light. , 2018, , .		0
172	Hybrid-plasmonic gold coated GaAs nanowire lasers. , 2018, , .		0
173	Engineering III-V nanowires for optoelectronics: from epitaxy to terahertz photonics. , 2018, , .		0
174	Engineering semiconductor nanowires for photodetection: from visible to terahertz. , 2018, , .		0
175	Probing the photophysics of semiconductor nanomaterials using optical pump-terahertz probe spectroscopy: from nanowires to perovskites. , 2018, , .		0
176	Radiation effects on GaAs/AlGaAs core/shell ensemble nanowires and nanowire infrared photodetectors. Nanotechnology, 2017, 28, 125702.	1.3	14
177	Single n⁺-i-n⁺InP nanowires for highly sensitive terahertz detection. Nanotechnology, 2017, 28, 125202.	1.3	26
178	Nonlinear Optical Magnetism Revealed by Second-Harmonic Generation in Nanoantennas. Nano Letters, 2017, 17, 3914-3918.	4.5	100
179	Engineering Highly Interconnected Neuronal Networks on Nanowire Scaffolds. Nano Letters, 2017, 17, 3369-3375.	4.5	58
180	Growth and optical properties of In x Ga1â^'x P nanowires synthesized by selective-area epitaxy. Nano Research, 2017, 10, 672-682.	5.8	24

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181	3D Atomic-Scale Insights into Anisotropic Core-Shell-Structured InGaAs Nanowires Grown by Metal-Organic Chemical Vapor Deposition. Advanced Materials, 2017, 29, 1701888.	11.1	15
182	The influence of surfaces on the transient terahertz conductivity and electron mobility of GaAs nanowires. Journal Physics D: Applied Physics, 2017, 50, 224001.	1.3	31
183	Strong Amplified Spontaneous Emission from High Quality GaAs_{1â€“x}Sb_x Single Quantum Well Nanowires. Journal of Physical Chemistry C, 2017, 121, 8636-8644.	1.5	15
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